查询KTC4793供应商 捷多邦，专业PCB打样工厂，24小时加急出货

KEC

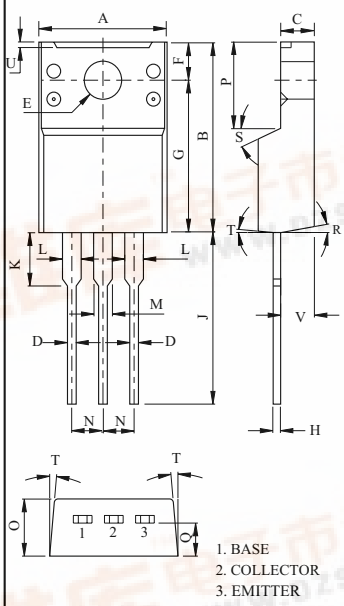
SEMICONDUCTOR
TECHNICAL DATA

KTC4793
TRIPLE DIFFUSED NPN TRANSISTOR

POWER AMPLIFIER APPLICATIONS.
DRIVER STAGE AMPLIFIER APPLICATINS.

FEATURES

· High Transition Frequency : f_T=100MHz(Typ.)
· Complementary Pair with KTA1837.



DIM	MILLIMETERS
A	10.30 MAX
B	15.30 MAX
C	2.70±0.30
D	0.85 MAX
E	Ø3.20±0.20
F	3.00±0.30
G	12.30 MAX
H	0.75 MAX
J	13.60±0.50
K	3.90 MAX
L	1.20
M	1.30
N	2.54
O	4.50±0.20
P	6.80
Q	2.60±0.20
R	10°
S	25°
T	5°
U	0.5
V	2.60±0.15

TO-220IS

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	230	V
Collector-Emitter Voltage		V_{CEO}	230	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current		I_C	1	A
Base Current		I_B	0.1	A
Collector Power Dissipation	Ta=25℃	P_C	2.0	W
	Tc=25℃		20	
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=230V, I_E=0	-	-	1.0	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=10mA, I_B=0	230	-	-	V
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=100mA	100	-	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA	-	-	1.5	V
Base-Emitter Voltage	V_{BE}	V_{CE}=5V, I_C=500mA	-	-	1.0	V
Transition Frequency	f_T	V_{CE}=10V, I_C=100mA	-	100	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	20	-	pF

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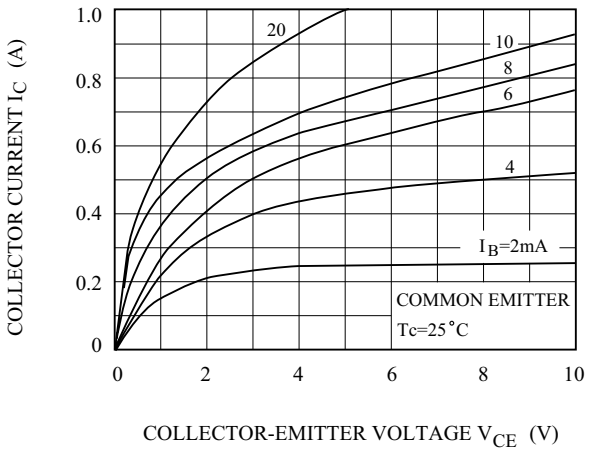
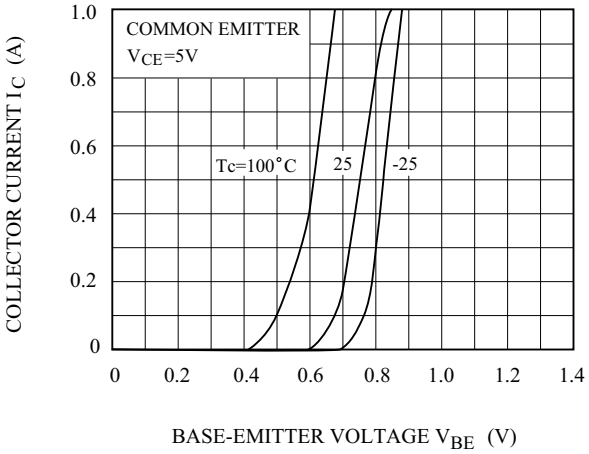
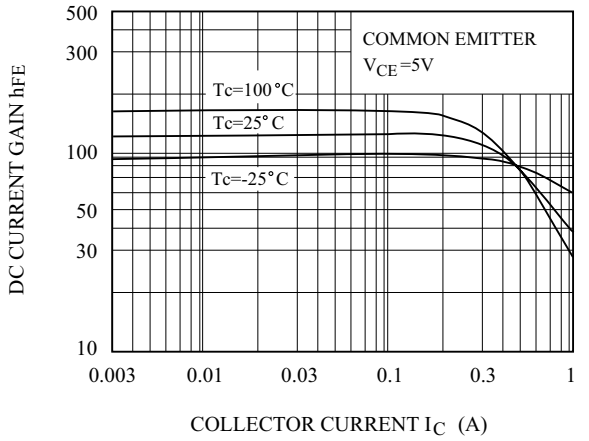
I_C - V_{CE}



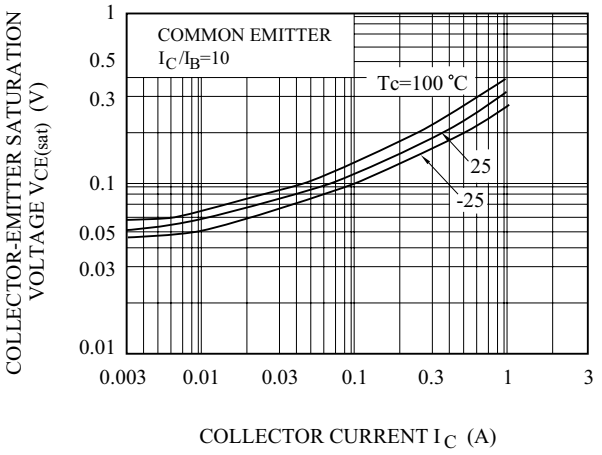
I_C - V_{BE}



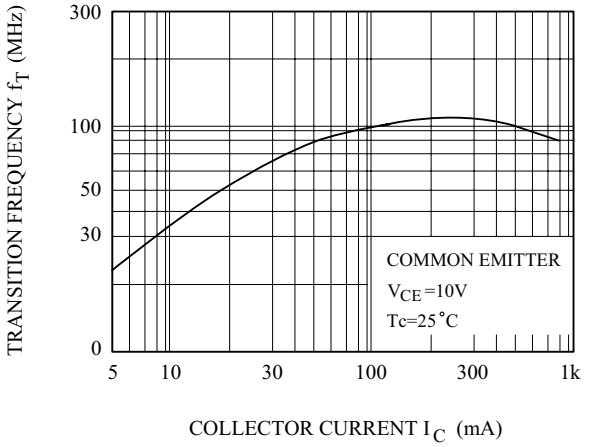
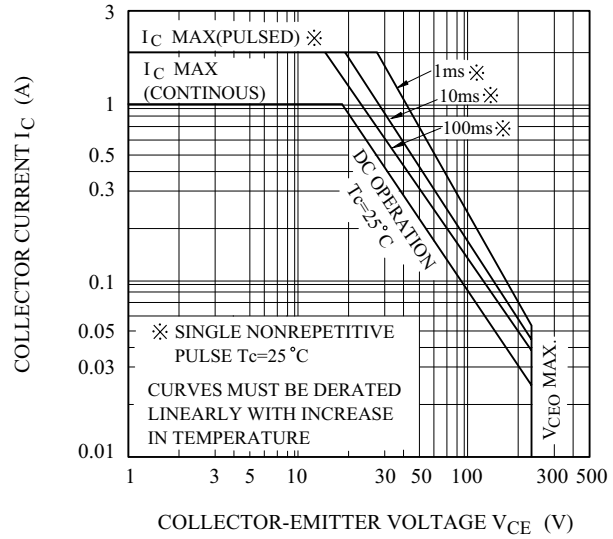
h_{FE} - I_C



$V_{CE(sat)}$ - I_C



f_T - I_C



SAFE OPERATING AREA